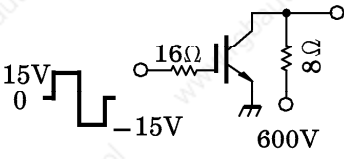


ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I _{GES}	V _{GE} = ±20V, V _{CE} = 0	—	—	±10	μA
Collector Cut-off Current		I _{CES}	V _{CE} = 1200V, V _{GE} = 0	—	—	1.0	mA
Gate-Emitter Cut-off Voltage		V _{GE(OFF)}	I _C = 75mA, V _{CE} = 5V	3.0	—	6.0	V
Collector-Emitter Saturation Voltage		V _{CE(sat)}	I _C = 75A, V _{GE} = 15V	—	3.0	4.0	V
Input Capacitance		C _{ies}	V _{CE} = 10V, V _{GE} = 0 f = 1MHz	—	9000	—	pF
Switching Time	Rise Time	t _r		—	0.3	0.6	μs
	Turn-on Time	t _{on}		—	0.4	0.8	
	Fall Time	t _f		—	0.2	0.5	
	Turn-off Time	t _{off}		—	0.8	1.5	
Forward Voltage		V _F	I _F = 75A, V _{GE} = 0	—	2.0	3.0	V
Reverse Recovery Time		t _{rr}	I _F = 75A, V _{GE} = -10V di / dt = 100A / μs	—	0.25	0.5	μs
Thermal Resistance		R _{th(j-c)}	Transistor	—	—	0.22	°C / W
			Diode	—	—	0.8	

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